

Variant: Variant of PMP23126.1 GaN Daughter Card
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PMP23126.1 REV B Bill of Materials

Item #	Designator	Quantity	Value	PartNumber	Manufacturer	Description	PackageReference
1	PCB1	1		PMP23126.1	Any	Printed Circuit Board	
2	C1, C7, C8, C9, C10	5	0.1uF	C1005X7R1H104K050BB	TDK	CAP, CERM, 0.1 uF, 50 V, +/- 10%, X7R, 0402	402
3	C3, C28	2	68pF	C1005C0G1H680J050BA	TDK	CAP, CERM, 68 pF, 50 V, +/- 5%, C0G/NP0, 0402	402
4	C4	1	4.7uF	GCM21BR71C475KA73L	MuRata	CAP, CERM, 4.7 uF, 16 V, +/- 10%, X7R, AEC-Q200 Grade 1, 0805	805
5	C5, C6, C15, C16, C17, C19	6	100pF	04025A101FAT2A	AVX	CAP, CERM, 100 pF, 50 V, +/- 1%, C0G/NP0, 0402	402
6	C11, C12, C23	3	4.7uF	C1608X5R1V475K080AC	TDK	CAP, CERM, 4.7 uF, 35 V, +/- 10%, X5R, 0603	603
7	C13, C14	2	10uF	C3216X7R1E106M160AE	TDK	CAP, CERM, 10 uF, 25 V, +/- 20%, X7R, 1206_190	1206_190
8	C20, C22	2	2.2uF	GRT155R61E225KE13D	MuRata	CAP, CERM, 2.2 uF, 25 V, +/- 10%, X5R, AEC-Q200 Grade 3, 0402	402
9	C24, C25	2	0.022uF	C1206C223KDRACTU	Kemet	CAP, CERM, 0.022 uF, 1000 V, +/- 10%, X7R, AEC-Q200 Grade 1, 1206	1206
10	C26, C27	2	0.1uF	C1812W104KDRACTU	Kemet	CAP, CERM, 0.1 uF, 1000 V, +/- 10%, X7R, 1812	1812
11	D1, D2	2	20V	MBR0520LT1G	ON Semiconductor	Diode, Schottky, 20 V, 0.5 A, SOD-123	SOD-123
12	L1, L2	2		SDEM20161T-4R7MS	Cyntec	4.7uH Unshielded Inductor 1.1A 426mOhm Max 0806 (2016 Metric)	SMD2
13	L3	1		ACM2520-601-2P-T002	TDK	Coupled inductor, 0.2 A, 0.45 ohm, SMD	2.5x2mm
14	R1, R3, R4, R5	4	49.9	RC0402FR-0749R9L	Yageo America	RES, 49.9, 1%, 0.063 W, 0402	402
15	R2, R10	2	300	CRCW0402300RJNED	Vishay-Dale	RES, 300, 5%, 0.063 W, AEC-Q200 Grade 0, 0402	402
16	R6, R7	2	200k	ERJ-2RKF2003X	Panasonic	RES, 200 k, 1%, 0.1 W, 0402	402
17	T1	1	475uH	760390014	Würth Elektronik	Transformer, 475uH, SMT	10.05x4.19x6.73 mm
18	U1	1		SN6505BDBVR	Texas Instruments	Low-Noise 1 A, 420 kHz Transformer Driver, DBV0006A (SOT-23-6)	DBV0006A
19	U3, U4	2		ISO7721FDWV	Texas Instruments	High Speed, Robust EMC Reinforced Dual-Channel Digital Isolator, DWV0008A (SOIC-8)	DWV0008A
20	U5, U6	2		XMG3522R050QRQSTQ1	Texas Instruments	650-V 30-mΩ GaN FET with Integrated Driver, Protection, and Temperature Reporting	VQFN52
21	C18, C21	0	0.22uF	CL05B224KO5NNNC	Samsung Electro-Mechanics	CAP, CERM, 0.22 uF, 16 V, +/- 10%, X7R, 0402	402
22	D3	0	600V	ES1JAF	Fairchild Semiconductor	Diode, Ultrafast, 600 V, 1 A, AEC-Q101, SMAF	SMAF